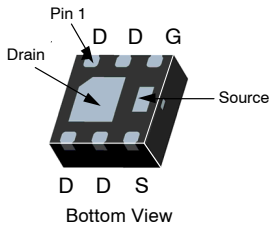
MOSFET – Single N-Channel, POWERTRENCH®

30 V, 9.0 A, 21 mΩ

FDMA7672



Bottom View

WDFN6 2x2, 0.65P
CASE 511CZ

General Description

This device has been designed to provide maximum efficiency and thermal performance for synchronous buck converters. The low $R_{DS(on)}$ and gate charge provide excellent switching performance.

Features

- Max $R_{DS(on)}$ = 21 mΩ @ V_{GS} = 10 V, I_D = 9.0 A
- Max $R_{DS(on)}$ = 32 mΩ @ V_{GS} = 4.5 V, I_D = 7 A
- Low Profile – 0.8 mm Maximum – in the New Package MicroFET™ 2x2 mm
- This Device is Pb-Free, Halide Free and RoHS Compliant

Applications

- DC-DC Buck Converters

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C unless otherwise noted)

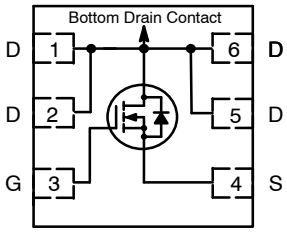
Symbol	Parameter		Value	Unit
V_{DSS}	Drain to Source Voltage		30	V
V_{GSS}	Gate to Source Voltage		±20	V
I_D	Drain Current – Continuous (Note 1a) – Pulsed	T_A = 25 °C	 9 24	A
P_D	Power Dissipation (Note 1a) Power Dissipation (Note 1b)	T_A = 25 °C T_A = 25 °C	2.4 0.9	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range		–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

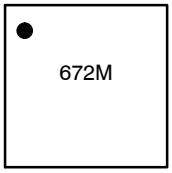
Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	6.9	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	52	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	145	

PIN CONNECTIONS



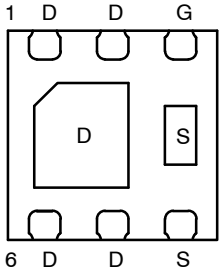
Top View

MARKING DIAGRAM



672 = Device Code
M = Month Code

PIN ASSIGNMENT



Bottom View

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_A = 25 °C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25 °C		16		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V			100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	1.0	2.1	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25 °C		−6		mV/°C
$R_{DS(on)}$	Static Drain to Source On-Resistance	V_{GS} = 10 V, I_D = 9.0 A		14	21	mΩ
		V_{GS} = 4.5 V, I_D = 7 A		20	32	
		V_{GS} = 10 V, I_D = 9 A, T_J = 125 °C		19	28	
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 9.0 A		35		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0 V, f = 1.0 MHz		570	760	pF
C_{oss}	Output Capacitance			195	260	
C_{rss}	Reverse Transfer Capacitance			25	40	
R_G	Gate Resistance			1.5		Ω
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 15 V, I_D = 9.0 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		6	12	ns
t_r	Rise Time			2	10	
$t_{d(off)}$	Turn-Off Delay Time			14	25	
t_f	Fall Time			2	10	
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V, V_{DD} = 15 V, I_D = 9.0 A		9.3	13	nC
		V_{GS} = 0 V to 4.5 V, V_{DD} = 15 V, I_D = 9.0 A		4.4	6	
Q_{gs}	Gate to Source Gate Charge	V_{DD} = 15 V, I_D = 9.0 A		1.9		
Q_{gd}	Gate to Drain “Miller” Charge			1.5		
DRAIN-SOURCE DIODE CHARACTERISTICS						
I_S	Maximum Continuous Drain-Source Diode Forward Current				2	A
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 2.0 A (Note 2)		0.8	1.2	V
t_{rr}	Reverse Recovery Time	I_F = 9.0 A, di/dt = 100 A/μs		18	32	ns
Q_{rr}	Reverse Recovery Charge			5	10	nC

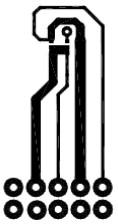
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user’s board design.



a.) 52 °C/W when mounted on a 1 in^2 pad of 2 oz. copper.



b.) 145 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%

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TYPICAL CHARACTERISTICS

(T_J = 25 °C unless otherwise noted)

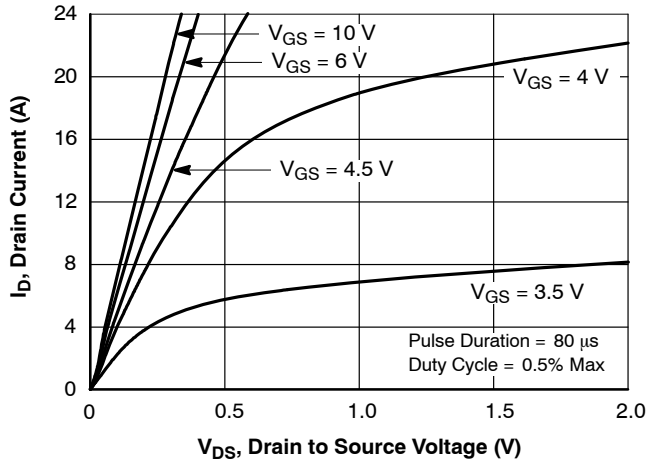


Figure 1. On-Region Characteristics

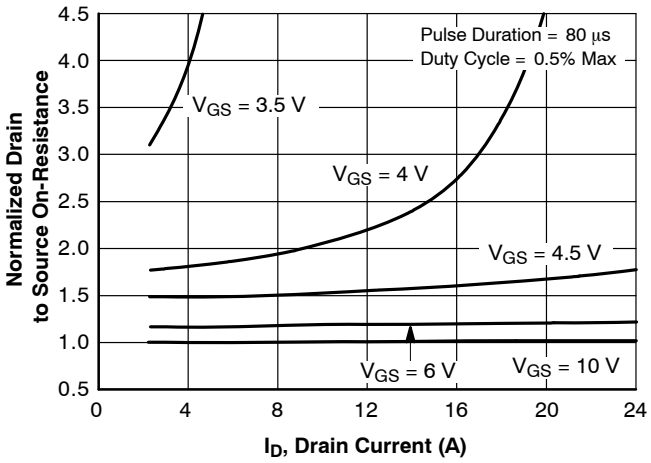


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

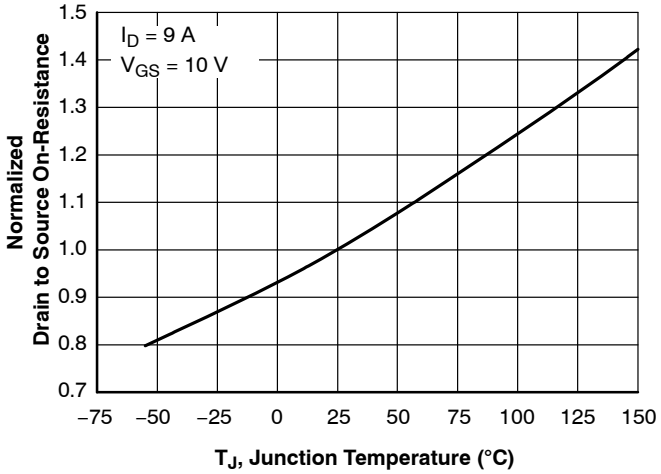


Figure 3. Normalized On-Resistance vs. Junction Temperature

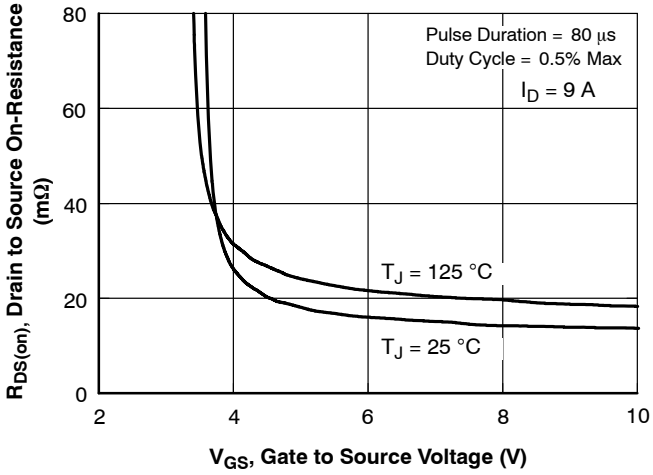


Figure 4. On-Resistance vs. Gate to Source Voltage

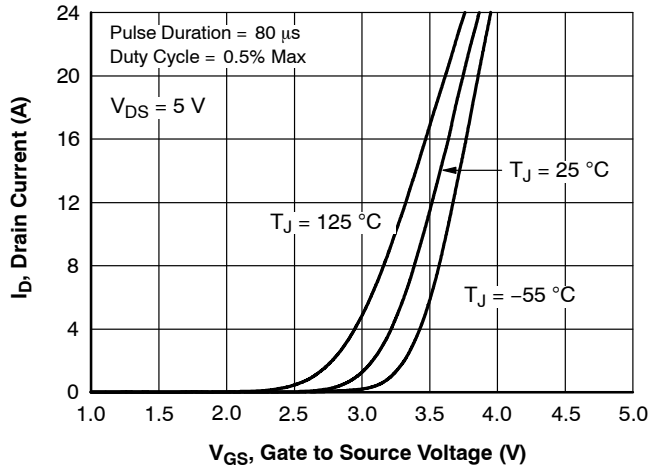


Figure 5. Transfer Characteristics

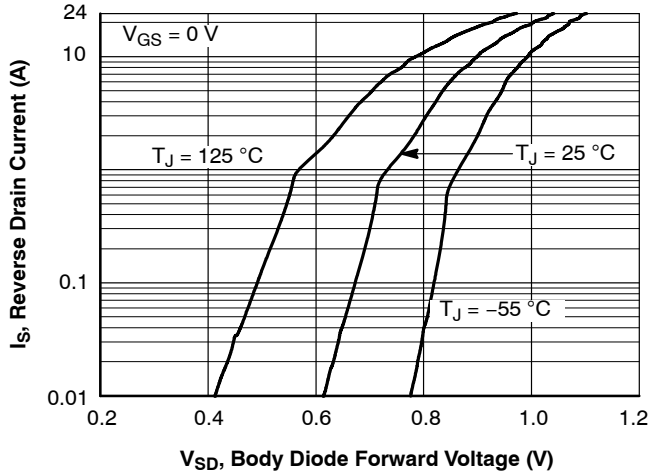


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

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TYPICAL CHARACTERISTICS (continued)

(T_J = 25 °C unless otherwise noted)

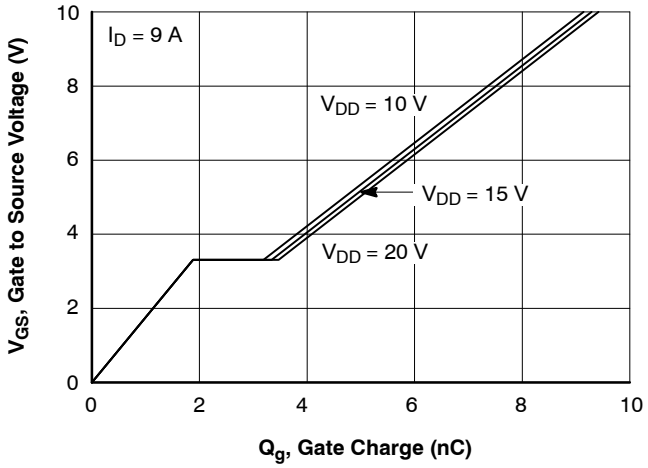


Figure 9. Gate Charge Characteristics

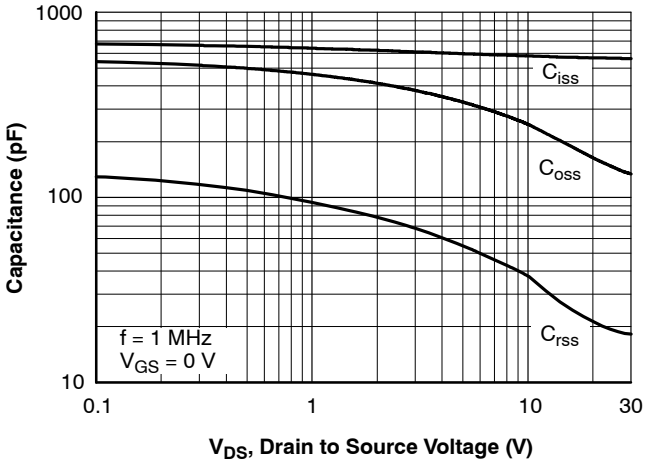


Figure 10. Capacitance vs. Drain to Source Voltage

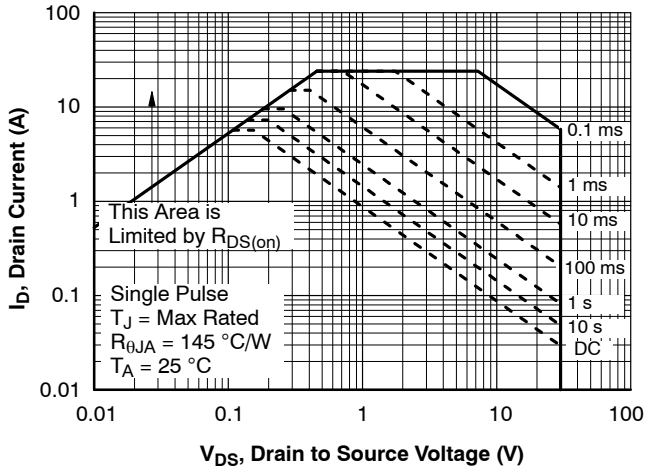


Figure 7. Forward Bias Safe Operating Area

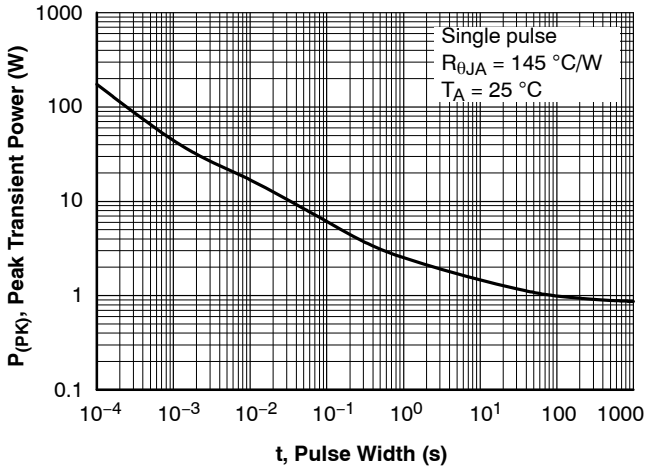


Figure 8. Single Pulse Maximum Power Dissipation

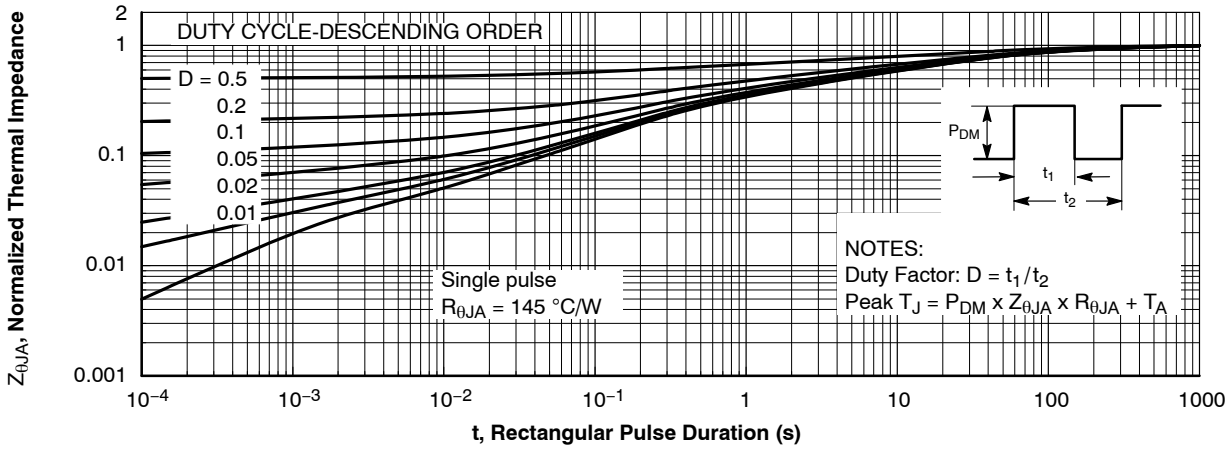


Figure 11. Transient Thermal Response Curve

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ORDERING INFORMATION

Device	Device Marking	Package Type	Reel Size	Tape Width	Shipping†
FDMA7672	672	WDFN6 2x2, 0.65P (Pb-Free/Halide Free)	7”	8 mm	3,000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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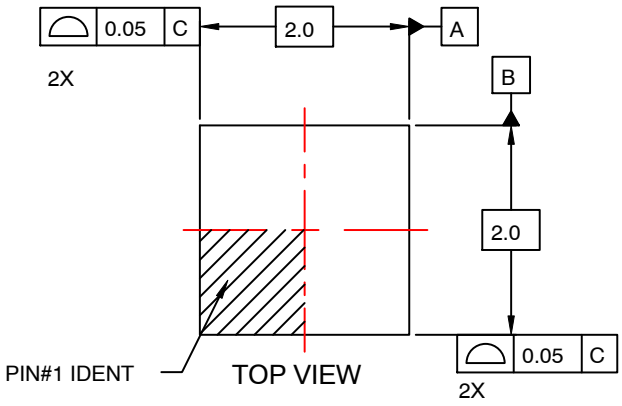
Revision	Description of Changes	Date
4	Marking Diagram update.	10/30/2026

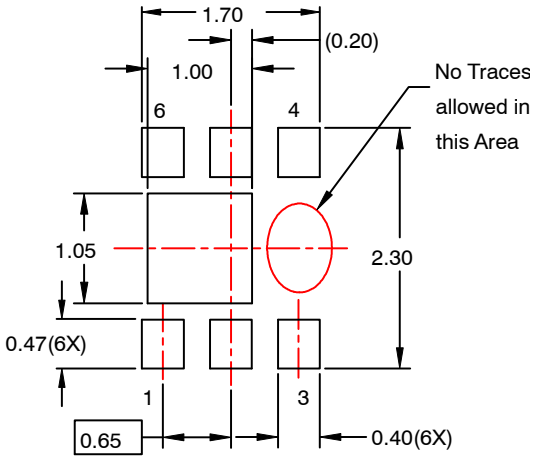
This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

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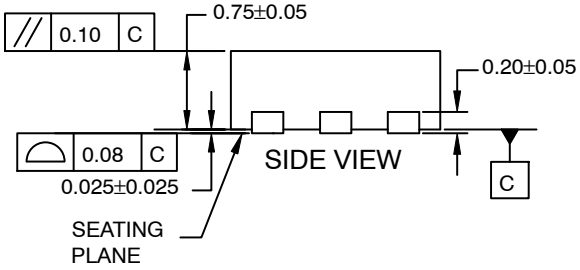
WDFN6 2x2, 0.65P
CASE 511CZ
ISSUE O

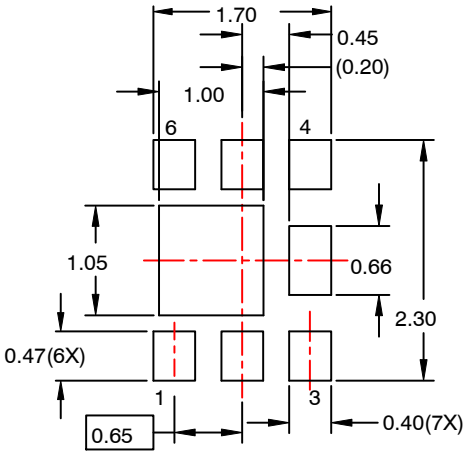
DATE 31 JUL 2016



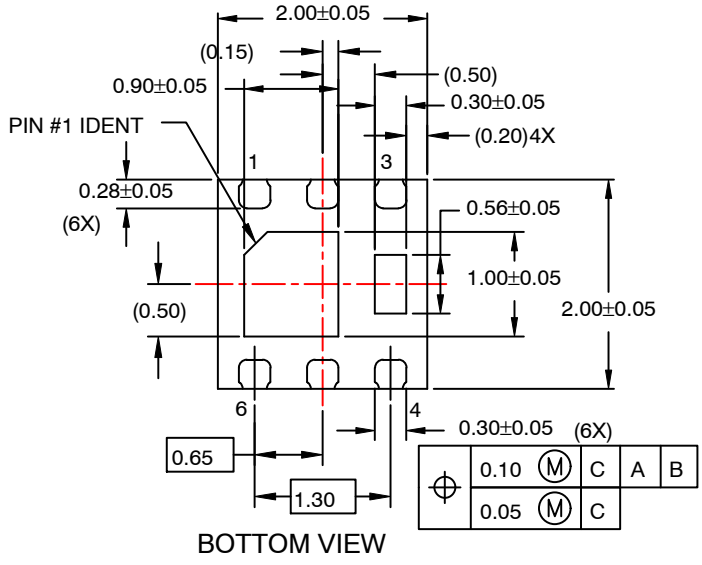


RECOMMENDED
LAND PATTERN OPT 1





RECOMMENDED
LAND PATTERN OPT 2



NOTES:

A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC MO−229 REGISTRATION

B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.

D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.

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DESCRIPTION:	**WDFN6 2X2, 0.65P**		**PAGE 1 OF 1**

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